



SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

P-Channel Silicon MOSFET

ATP103 — General-Purpose Switching Device Applications

Features

- Low ON-resistance
- Slim package
- Halogen free compliance
- Large current
- 4.5V drive
- Protection diode in

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		-30	V
Gate-to-Source Voltage	V _{GSS}		±20	V
Drain Current (DC)	I _D		-55	A
Drain Current (PW≤10μs)	I _{DP}	PW≤10μs, duty cycle≤1%	-165	A
Allowable Power Dissipation	P _D	Tc=25°C	50	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C
Avalanche Energy (Single Pulse) *1	E _{AS}		57	mJ
Avalanche Current *2	I _{AV}		-28	A

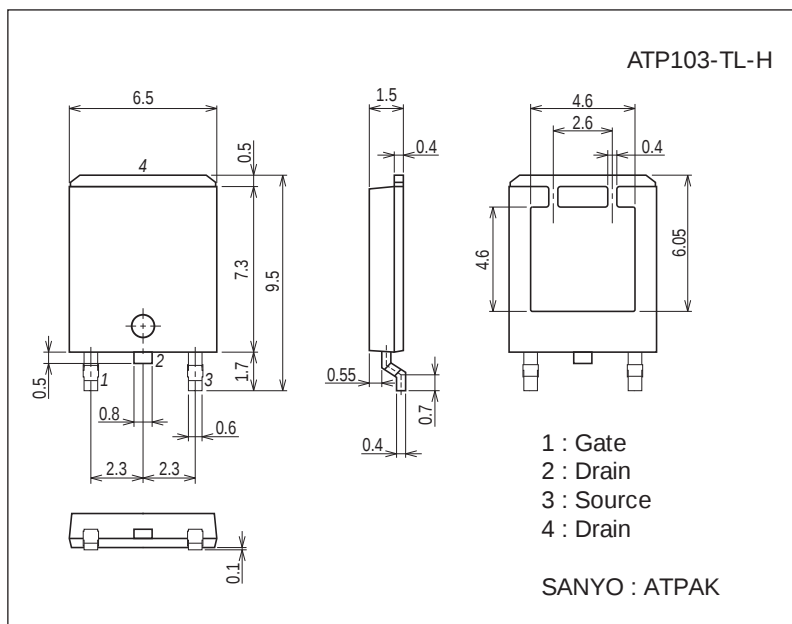
Note : *1 V_{DD}=-10V, L=100μH, I_{AV}=-28A

*2 L≤100μH, Single pulse

Package Dimensions

unit : mm (typ)

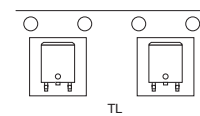
7057-001



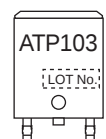
Product & Package Information

- Package : ATPAK
- JEITA, JEDEC : -
- Minimum Packing Quantity : 3,000 pcs./reel

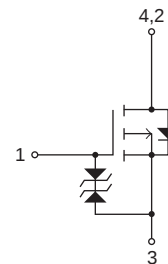
Packing Type: TL



Marking



Electrical Connection

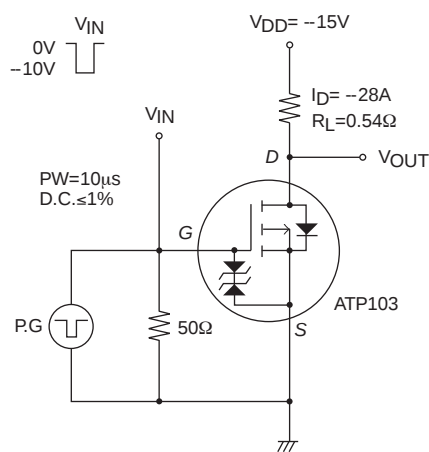


ATP103

Electrical Characteristics at Ta=25°C

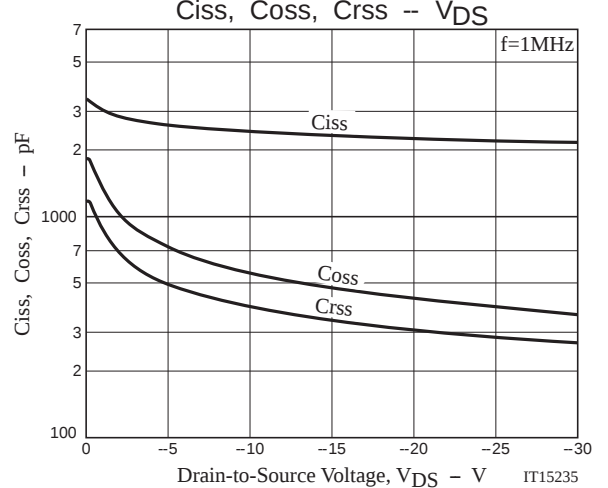
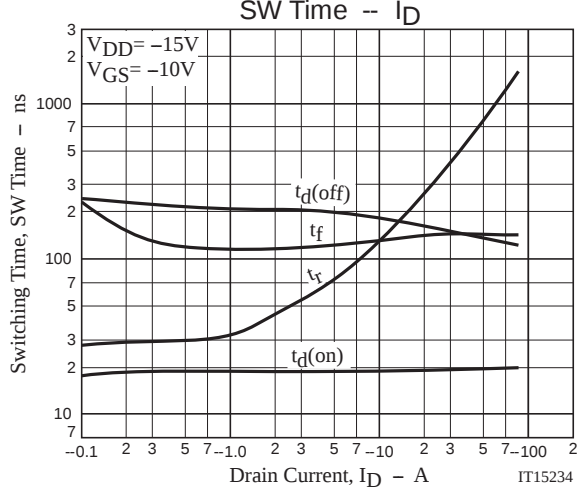
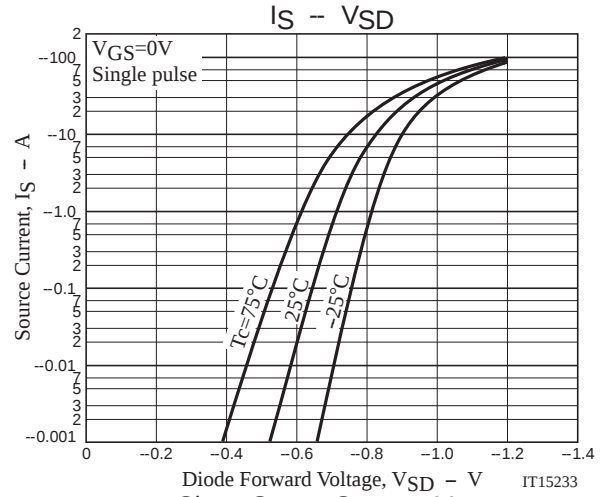
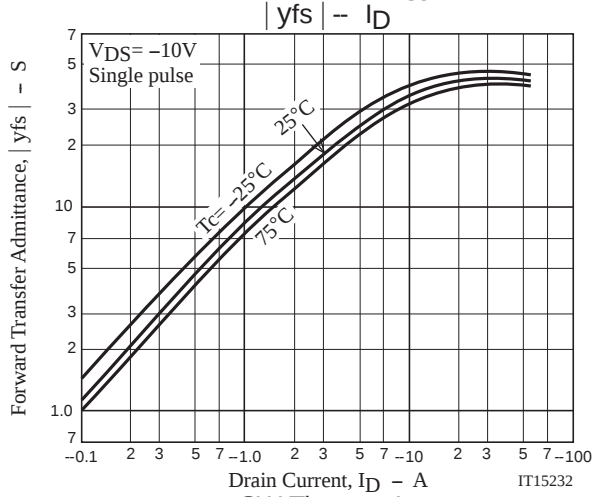
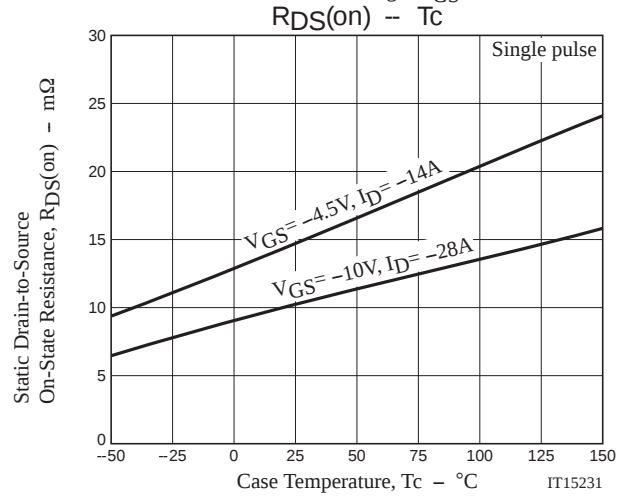
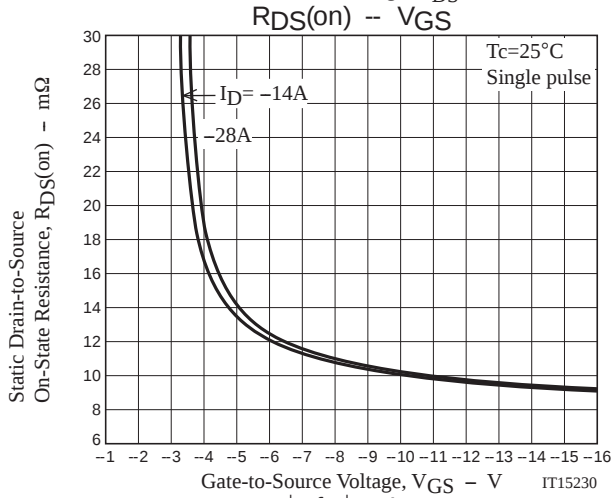
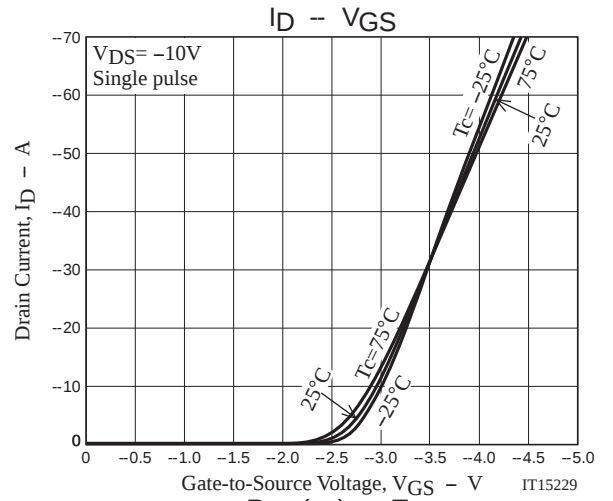
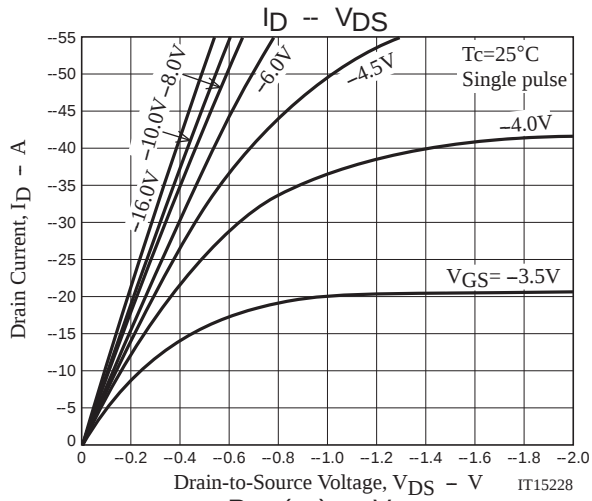
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=-1mA, V_{GS}=0V$	-30			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-30V, V_{GS}=0V$			-1	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 16V, V_{DS}=0V$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=-10V, I_D=-1mA$	-1.2		-2.6	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=-10V, I_D=-28A$		45		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=-28A, V_{GS}=-10V$		10	13	$m\Omega$
	$R_{DS(on)2}$	$I_D=-14A, V_{GS}=-4.5V$		14.5	20.5	$m\Omega$
Input Capacitance	C_{iss}	$V_{DS}=-10V, f=1MHz$		2430		pF
Output Capacitance	C_{oss}			555		pF
Reverse Transfer Capacitance	C_{rss}			395		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		19		ns
Rise Time	t_r			400		ns
Turn-OFF Delay Time	$t_{d(off)}$			150		ns
Fall Time	t_f			145		ns
Total Gate Charge	Q_g	$V_{DS}=-15V, V_{GS}=-10V, I_D=-55A$		47		nC
Gate-to-Source Charge	Q_{gs}			10		nC
Gate-to-Drain "Miller" Charge	Q_{gd}			8.7		nC
Diode Forward Voltage	V_{SD}	$I_S=-55A, V_{GS}=0V$		-1.03	-1.5	V

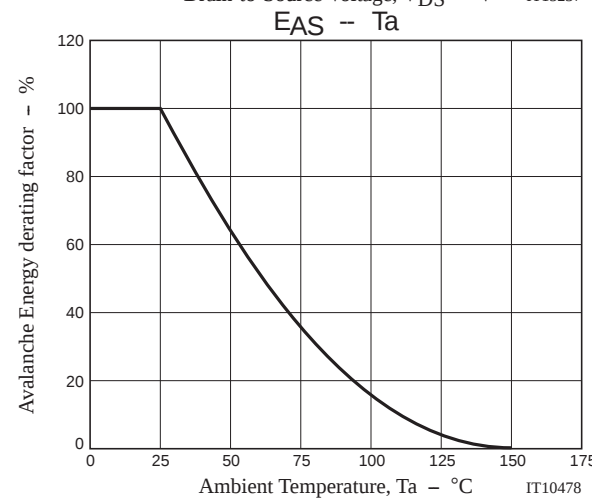
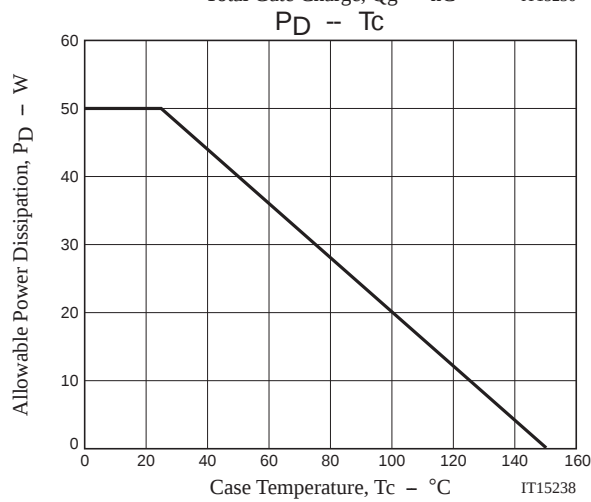
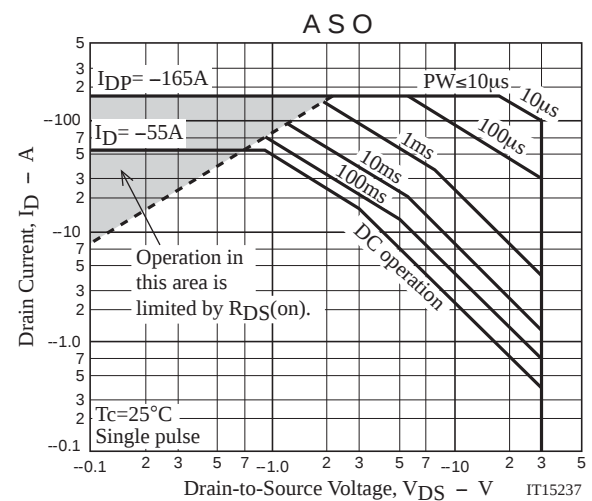
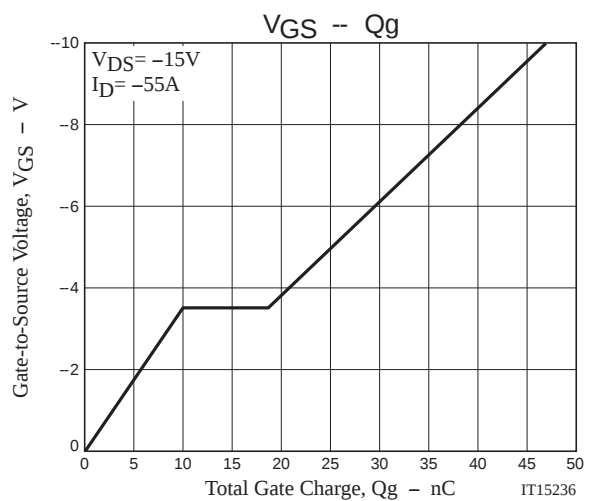
Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo
ATP103-TL-H	ATPAK	3,000pcs./reel	Pb Free and Halogen Free





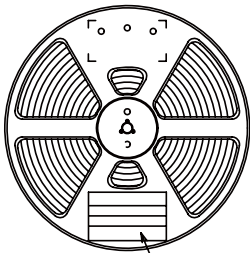
Taping Specification

ATP103-TL-H

1. Packing Format (TL)

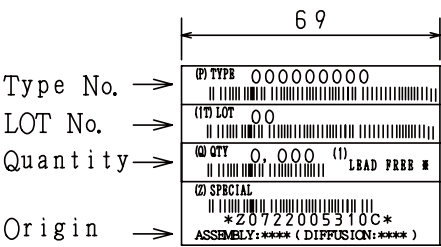
Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	INNER BOX SD-C-18	OUTER BOX SD-A-18
ATPAK	ATP	3,000	3,000	15,000	1 reels contained Dimensions:mm (external) 340×340×28	5 inner boxes contained Dimensions:mm (external) 355×355×165

Packing method



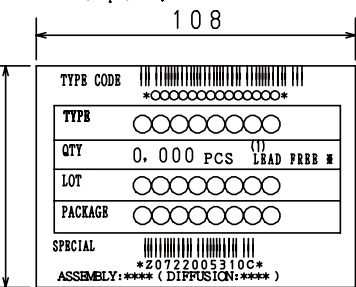
Reel label

Reel label, Inner box label
(unit:mm)



Outer box label

It is a label at the time of factory shipments.
The form of a label may change in physical distribution process.



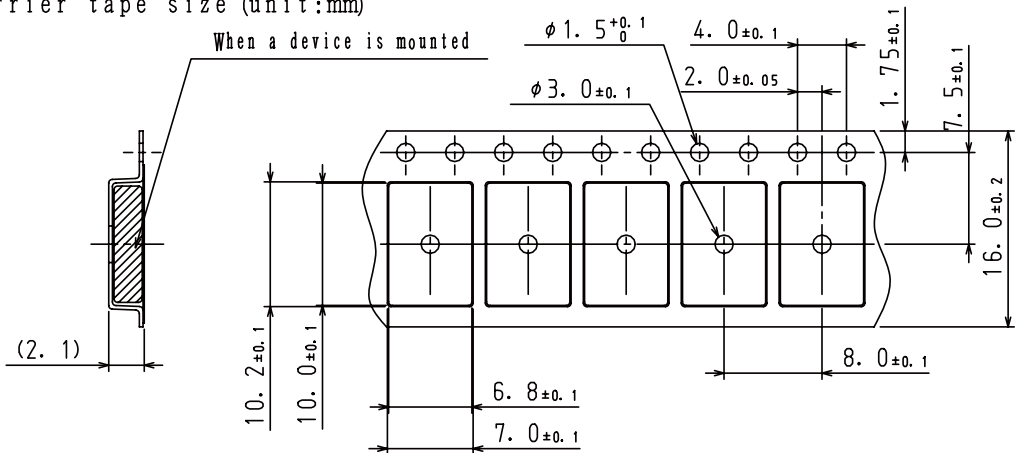
NOTE (1)

The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

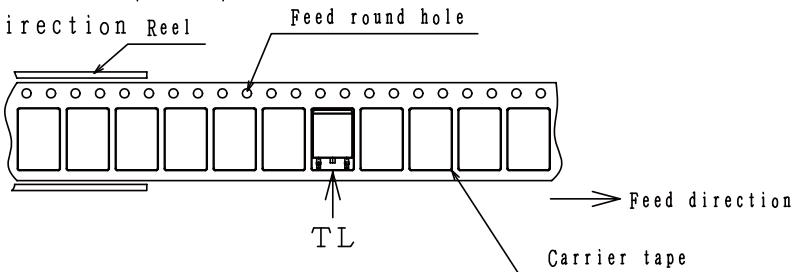
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



2-2. Device placement direction Reel

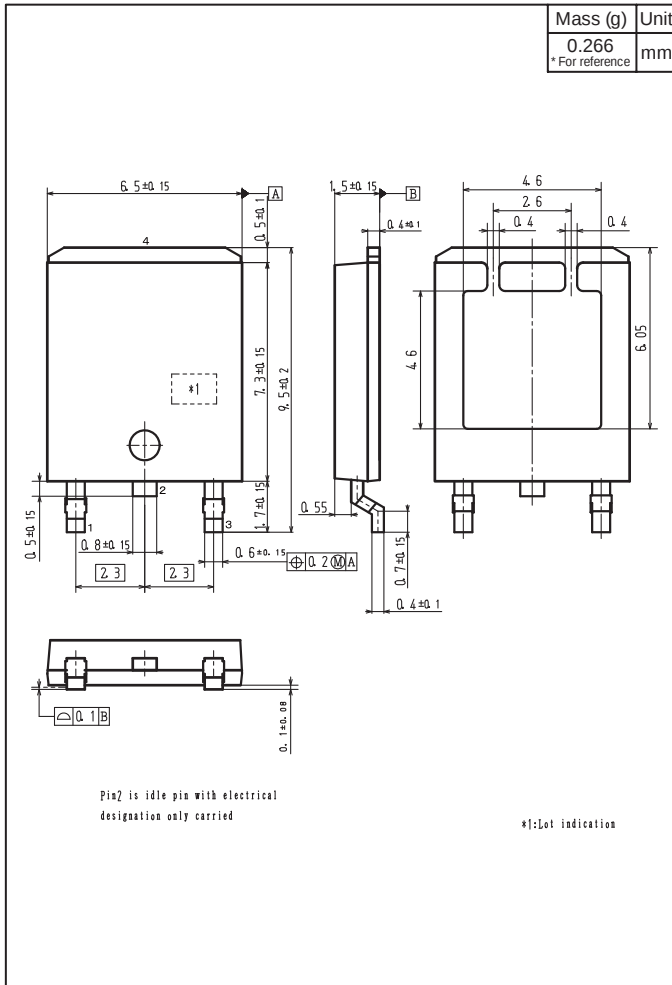


The one electrode terminals on feed hole side...TL

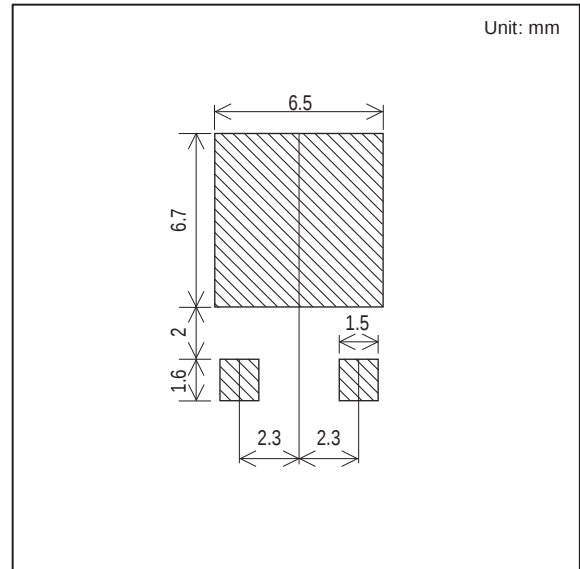
ATP103

Outline Drawing

ATP103-TL-H



Land Pattern Example



Note on usage : Since the ATP103 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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